

ABSTRACT

The process of the present invention comprises reactive ion etching of $Al_xF_yO_z$ oxide deposits on aluminum-containing bond pads using feed gases, such as, $SF_6/CF_4/Ar$ or $Cl_2/BCL_3/Ar$, whose active plasma etches the $Al_xF_yO_z$ oxide deposits by physical etching and chemical etching for more complete removal of the $Al_xF_yO_z$ oxide deposits.